

DRAF114E

Silicon PNP epitaxial planar type

For digital circuits

Complementary to DRCF114E

DRA3114E in ML3 type package

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Contributes to miniaturization of sets, mount area reduction
- Eco-friendly Halogen-free package

■ Packaging

DRAF114E0L Embossed type (Thermo-compression sealing): 10000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-50	V
Collector-emitter voltage (Base open)	V_{CEO}	-50	V
Collector current	I_C	-100	mA
Total power dissipation *	P_T	100	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *: Copper plate at the collector is 5.0 mm² on substrate at 10 mm × 12 mm × 0.8 mm.

■ Package

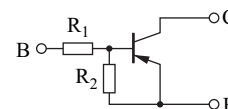
- Code
ML3-N4-B
Package dimension clicks here.→

• Pin Name

- 1: Base
- 2: Emitter
- 3: Collector

■ Marking Symbol: LB

■ Internal Connection



Resistance value	R_1	10	k Ω
	R_2	10	k Ω

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-50			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -2 \text{ mA}, I_B = 0$	-50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$			-0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -50 \text{ V}, I_B = 0$			-0.5	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -6 \text{ V}, I_C = 0$			-0.5	mA
Forward current transfer ratio	h_{FE}	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	35			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$			-0.25	V
Input voltage (ON)	$V_{I(on)}$	$V_{CE} = -0.2 \text{ V}, I_C = -5 \text{ mA}$	-2.1			V
Input voltage (OFF)	$V_{I(off)}$	$V_{CE} = -5 \text{ V}, I_C = -100 \mu\text{A}$			-0.8	V
Input resistance	R_1		-30%	10	+30%	k Ω
Resistance ratio	R_1 / R_2		0.8	1.0	1.2	—

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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